Gioele Mirabelli

List of Publications by Year
in descending order

18	377	1039406 9	1058022 14
papers	citations	h-index	g-index

18	18	18	901
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Air sensitivity of MoS2, MoSe2, MoTe2, HfS2, and HfSe2. Journal of Applied Physics, 2016, 120, .	1.1	134
2	Quantum confinement-induced semimetal-to-semiconductor evolution in large-area ultra-thin PtSe2 films grown at 400â€‰Â°C. Npj 2D Materials and Applications, 2019, 3, .	3.9	69
3	Evaluation of border traps and interface traps in HfO ₂ /MoS ₂ gate stacks by capacitanceâ€“voltage analysis. 2D Materials, 2018, 5, 031002.	2.0	63
4	Back-gated Nb-doped MoS2 junctionless field-effect-transistors. AIP Advances, 2016, 6, .	0.6	20
5	Physics-based modelling of MoS₂: the layered structure concept. Semiconductor Science and Technology, 2019, 34, 055015.	1.0	13
6	Investigating the transient response of Schottky barrier back-gated MoS₂ transistors. 2D Materials, 2020, 7, 025040.	2.0	13
7	Exploring conductivity in ex-situ doped Si thin films as thickness approaches 5â€‰nm. Journal of Applied Physics, 2019, 125, 225709.	1.1	12
8	Effects of Annealing Temperature and Ambient on Metal/PtSe₂ Contact Alloy Formation. ACS Omega, 2019, 4, 17487-17493.	1.6	10
9	Monolayer doping of silicon-germanium alloys: A balancing act between phosphorus incorporation and strain relaxation. Journal of Applied Physics, 2019, 126, .	1.1	9
10	Formation and characterization of Ni, Pt, and Ti stanogermanide contacts on Ge0.92Sn0.08. Thin Solid Films, 2019, 690, 137568.	0.8	9
11	Cell formation in stanogermanides using pulsed laser thermal anneal on Ge0.91Sn0.09. Materials Science in Semiconductor Processing, 2021, 121, 105399.	1.9	8
12	Structural and Electrical Investigation of MoS₂Thin Films Formed by Thermal Assisted Conversion of Mo Metal. ECS Journal of Solid State Science and Technology, 2016, 5, Q3016-Q3020.	0.9	6
13	AsH3 gas-phase ex situ doping 3D silicon structures. Journal of Applied Physics, 2018, 124, .	1.1	4
14	Impact of impurities, interface traps and contacts on MoS<inf>2</inf> MOSFETs: Modelling and experiments. , 2017, , .		3
15	Hall-effect mobility for a selection of natural and synthetic 2D semiconductor crystals. , 2017, , .		2
16	Monolayer doping and other strategies in high surface-to-volume ratio silicon devices. , 2018, , .		1
17	Tertiarybutylarsine damage-free thin-film doping and conformal surface coverage of substrate-released horizontal Si nanowires. Applied Surface Science, 2020, 508, 145147.	3.1	1
18	Ex-situ plasma doping of MoS<inf>2</inf> thin films synthesised by thermally assisted conversion process: Simulations and experiment. , 2017, , .		0